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Micro-spectrometer

C12666MA

Finger-tip size, ultra-compact spectrometer head integrating MEMS and image sensor technologies

The C12666MA is an ultra-compact (Finger-tip size) spectrometer head developed based on our MEMS and image sensor technologies. The adoption of a newly designed optical system has achieved a remarkably small size, less than half the volume of the previous mini-spectrometer MS series (C10988MA-01). In addition, the employment of hermetic packaging has improved humidity resistance.

This product is suitable for integration into a variety of devices, such as integration into printers and hand-held color monitoring devices that require color management. It is also suitable for applications that collaborate with portable devices, such as smartphones and tablets.

Features

- ➡ Finger-tip size: 20.1 × 12.5 × 10.1 mm
- Weight: 5 g
- Spectral response range: 340 to 780 nm
- Spectral resolution: 15 nm max.
- Hermetic package: High reliability against humidity
- Installation into mobile measurement equipment
- ➡ Wavelength conversion factor*¹ is listed on final inspection sheet

Applications

- Color monitoring for printers and printing machines
- Testers for lights and LEDs
- Color adjustment of various large size displays
- Water quality control monitors and other environment measuring instruments
- Measuring instruments that use portable devices such as smartphones and tablets
- *1: A conversion factor for converting the image sensor pixel number into a wavelength. A calculation factor for converting the A/D converted count into the input light level is not provided.

Optical characteristics

Parameter	Value	Unit
Spectral response range	340 to 780	nm
Spectral resolution (FWHM)	15 max.	nm
Wavelength reproducibility*2	-0.5 to +0.5	nm
Wavelength temperature dependence	-0.1 to +0.1	nm/°C
Spectral stray light*3	-25	dB

*2: Measured under constant light input conditions

*3: Spectral stray light = $10 \times \log (TI/Th)$

Th: count measured when light at a certain wavelength is input

TI: count measured at a wavelength 40 nm longer or shorter than the input light wavelength

Electrical characteristics

Parameter	Min.	Тур.	Max.	Unit
Supply voltage	4.75	5	5.25	V
Power consumption	-	30	-	mW
Video rate	0.25	-	200	kHz
Output impedance	-	150 *4	-	Ω

*4: An increase in the current consumption at the video output terminal also increases the chip temperature and so causes the dark current to rise. To avoid this, connect a buffer amplifier for impedance conversion to the video output terminal so that the current flow is minimized. As the buffer amplifier, use a JFET or CMOS input operational amplifier of optical input impedance.

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Structure

Parameter	Specification	Unit
Dimensions (W \times D \times H)	H) 20.1 × 12.5 × 10.1	
Weight	5	g
Slit ^{*5} (H \times V)	50 × 750	μm
NA* ⁶	0.22	-
Image sensor $(H \times V)$	CMOS linear image sensor with a slit	-
Number of pixels	256	pixels
Pixel size (H \times V)	12.5 × 1000	μm

*5: Entrance slit aperture size

*6: Numeric aperture (solid angle)

Absolute maximum ratings

Parameter	Value	Unit
Operating temperature*7	+5 to +40	°C
Storage temperature*7	-20 to +70	°C

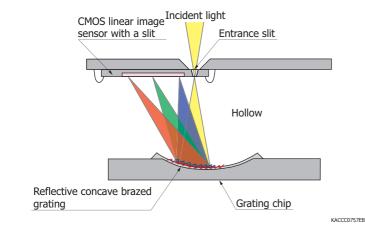
*7: No condensation

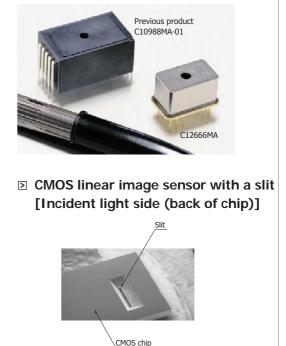
Note: Exceeding the absolute maximum ratings even momentarily may cause a drop in product quality. Always be sure to use the product within the absolute maximum ratings.

Optical component layout

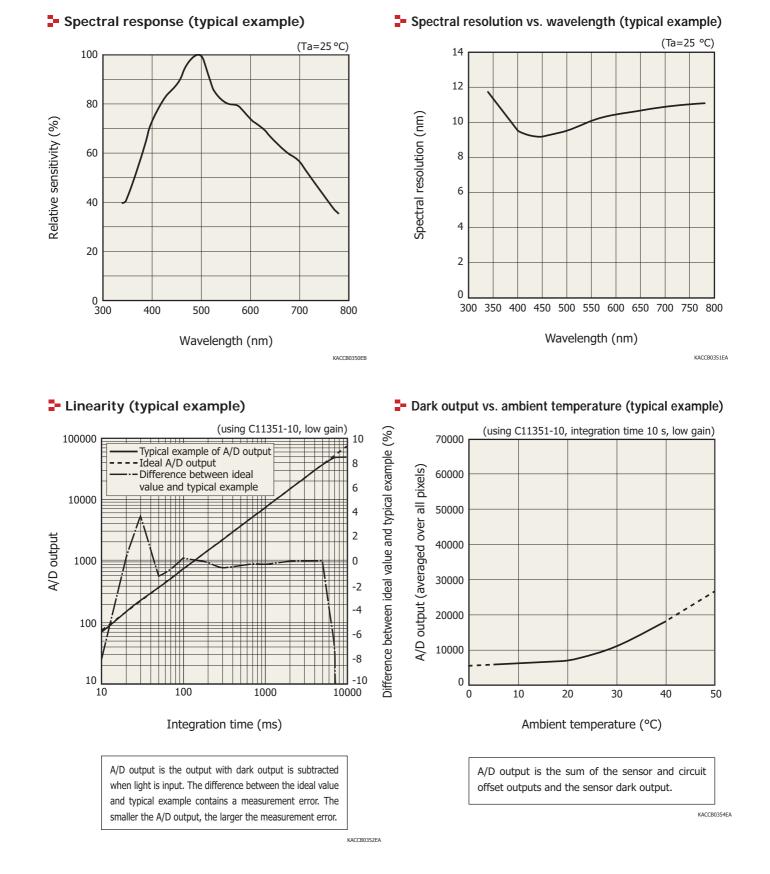
Besides a CMOS image sensor chip integrated with an optical slit by etching technology, the C12666MA employs a reflective concave brazed grating formed by nanoimprint. In addition, the glass used in the light path of the previous C10988MA-01 is not used in the C12666MA, making it extremely compact.

Structure





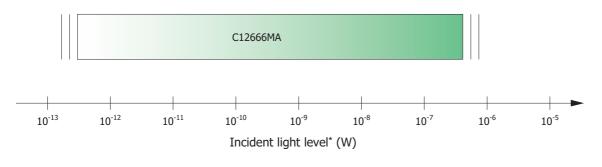




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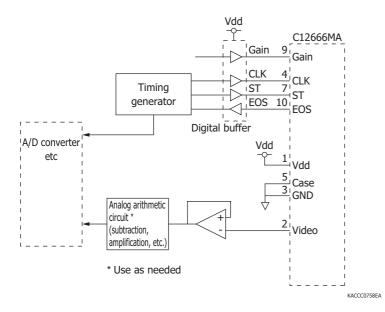
Measurable incident light level



* Input spot diameter: 800 μ m (λ =550 nm)

KACCB354EA

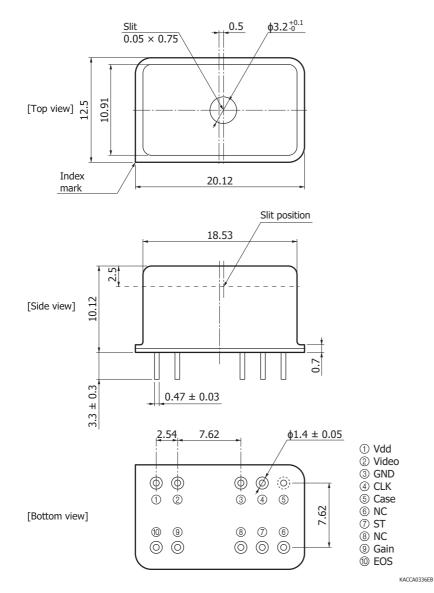
Recommended driver circuit example



Precautions

- The C12666MA is electrically conductive, so be careful when designing the circuit to avoid short circuit caused by contact with a circuit pattern.
- \cdot If external force is repeatedly applied to the lead pins, this may damage the lead pins.
- \cdot To prevent damage due to soldering, be careful of the soldering temperature and time.
- As a general guide, finish soldering within 3.5 seconds at 350 °C or less when soldering by hand, or within 10 seconds at 260 °C or less when using a solder bath.





Dimensional outline (unit: mm, tolerance unless otherwise noted: ±0.2)

Pin connections

Make electrical connections to an external circuit using leads.

Pin no.	Symbol	Name	I/O	Description
1	Vdd	Supply voltage	I	Image sensor power supply: 5 V
2	Video	Video output	0	Video output signal
3	GND	Ground	-	Sensor ground
4	CLK	Clock pulse	I	Sensor scan sync signal
5	Case	Case	-	Case connection terminal
6	NC		-	No connection
7	ST	Start pulse	I	Start pulse
8	NC		-	No connection
9	Gain	Gain	I	Image sensor: Gain setting
10	EOS	End of scan	0	Sensor scan end signal

Note: Pin no. 9 is pulled up internally to Vdd via 10 k Ω

Do not pull-up or pull-down the gain setting using an external circuit. For low gain, leave the pin open or connect to Vdd. For high gain, connect to GND.



Internal CMOS image sensor specifications

Recommended terminal voltage

Parameter		Symbol	Min.	Тур.	Max.	Unit
Supply voltage		Vdd	4.75	5	5.25	V
Gain selection terminal	High gain	Gain	0	-	0.4	V
voltage	Low gain	Gain	Vdd - 0.25	Vdd	Vdd + 0.25	V
Clock pulse voltage	High level		Vdd - 0.25	Vdd	Vdd + 0.25	V
	Low level	V(CLK)	0	-	0.4	V
Start pulse voltage	High level	V(ST)	Vdd - 0.25	Vdd	Vdd + 0.25	V
	Low level	V(ST)	0	-	0.4	V

Electrical characteristics

Parameter		Symbol	Min.	Тур.	Max.	Unit
Clock pulse frequency*8		f(CLK)	1	-	800	kHz
Power concumption	High gain	р	-	-	60	mW
Power consumption	Low gain		-	-	60	IIIVV

*8: Ta=25 °C, Vdd=5 V, V(CLK)=V(ST)=5

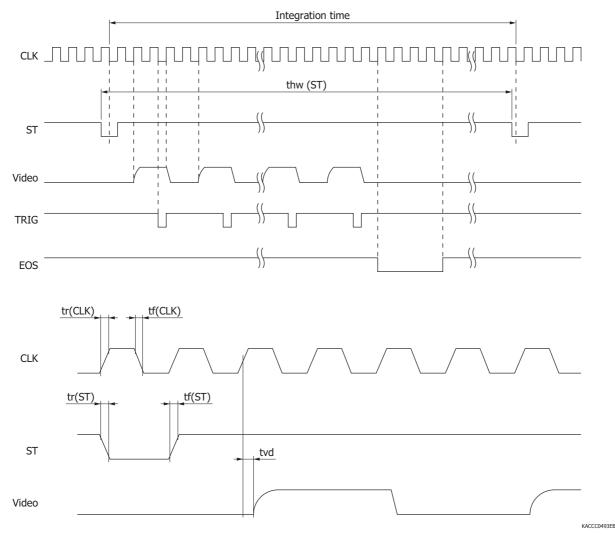
Electrical and optical characteristics

Parameter		Symbol	Min.	Тур.	Max.	Unit
Dark current	High gain	ID	-	0.02	0.08	۳۸
	Low gain		-	0.02	0.08	рА
Output offset voltage	High gain	Vo	0.15	0.35	0.55	V
	Low gain	VU	0.15	0.35	0.55	v
Charge amplifier feedback	High gain	Cf	-	1.4	-	рF
capacitance*9	Low gain		-	4.8	-	
Saturation output voltage*10	High gain	Vsat	2.3	2.8	3.3	V
Saturation output voltage	Low gain	vsat	1.4	1.7	2.0	v
Readout noise	High gain	Nr	-	0.3	0.5	mV rms
	Low gain		-	0.2	0.4	

*9: Gain=5 V (low gain), Vg=0 V (high gain) *10: Voltage difference relative to Vo



Timing chart



Parameter	Symbol	Min.	Тур.	Max.	Unit
Start pulse high period	thw(ST)	1030/f(CLK)	-	-	S
Start pulse rise/fall times	tr(ST), tf(ST)	0	20	30	ns
Clock pulse duty ratio	-	45	50	55	%
Clock pulse rise/fall times	tr(CLK), tf(CLK)	0	20	30	ns
Video delay time	tvd	-	20	-	ns

Note: The clock pulse should be set from high to low just once when the start pulse is low. The internal shift register starts operating at this timing.

The integration time is determined by the start pulse intervals. However, since the charge integration of each pixel is carried out between the signal readout of that pixel and the next signal readout of the same pixel, the start time of charge integration differs depending on each pixel. In addition, the next start pulse cannot be input until signal readout from all pixels is completed. Video output is 1/4 of the clock pulse frequency.



Micro-spectrometer evaluation circuit C11351-10 (sold separately)

The C11351-10 is a circuit board designed to simply evaluate the characteristics of the micro-spectrometer. The characteristics of the micro-spectrometer can be evaluated using the evaluation software by connecting the micro-spectrometer to a PC with a USB cable A9160 (AB type, sold separately)^{*11}.

Features

- Initial evaluation circuit for micro-spectrometer*12
- Wavelength conversion factors of the micro-spectrometer can be input from a PC.*13
- High A/D resolution (16-bit)
- USB powered
- *11: Compatible OS:



Microsoft[®] Windows[®] XP Professional SP3 (32-bit), Microsoft[®] Windows[®] Vista Business SP2 (32-bit) Microsoft[®] Windows[®] 7 Professional SP1 (32-bit), Microsoft[®] Windows[®] 7 Professional SP1 (64-bit) Microsoft and Windows are registered trademarks of Microsoft Corporation in the United States and/or other countries.

- *12: The C11351-10 is a modified version of the C11351 evaluation circuit for the previous mini-spectrometer MS series (C10988MA-01, C11708MA). Only the sensor board has been modified. If you already have the C11351, you only have to purchase the C11351-03 (the sensor board for micro-spectrometers) to evaluate C12666MA micro-spectrometers.
- *13: A typical wavelength conversion factor is entered at the time of shipment of the C11351-10. To measure a spectrum with higher wavelength accuracy, it is necessary to input the wavelength conversion factor listed in the final inspection sheet that comes with each micro-spectrometer.

Note: Since the C11351-10 is an evaluation circuit for the micro-spectrometer, the DLL function specifications are not available to users.

Electrical characteristics

Parameter	Specification	Unit
Interface	USB 2.0	-
A/D conversion	16	bit
Clock pulse frequency	800	kHz
Video rate	200	kHz
Integration time	5 to 10000	ms

Structure

Parameter		Specification	Unit
Applicable spectrometer		C12666MA	-
Dimensions Control board		80 × 60	mm
DIMENSIONS	Sensor board	30 × 44	mm

Absolute maximum ratings

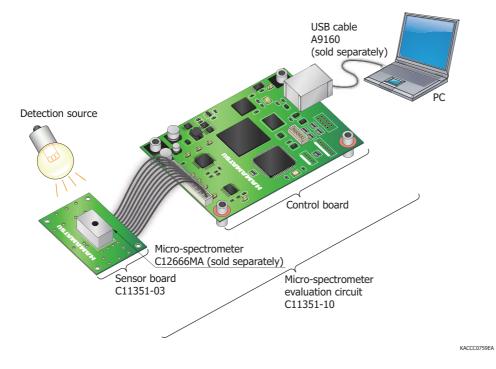
Parameter	Value	Unit
Operating temperature*14	+5 to +40	°C
Storage temperature*14	-20 to +70	°C

*14: No condensation

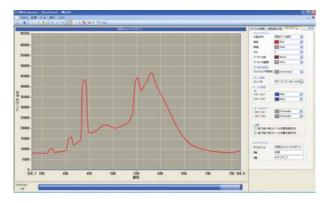
Note: Exceeding the absolute maximum ratings even momentarily may cause a drop in product quality. Always be sure to use the product within the absolute maximum ratings.



Connection example



Evaluation software display example





Mini-spectrometer/micro-spectrometer lineup

Type no.		Туре	20	ך ר	100	60	0	80	0 10				ral 1) 14								220	0	240	0.2	260		Spectral resolution max. (nm)	Image sensor				
C10082CA		TM-UV/VIS-CCD High sensitivity															10		200								6	Pack thinned to				
C10082CAH	1	TM-UV/VIS-CCD High resolution		20	00 to	o 8(00																				1*	Back-thinned typ CCD image sense				
C10082MD	neter	TM-UV/VIS-MOS Wide dynamic range																									6	CMOS linear image sensor				
C10083CA	Mini-spectrometer TM series	TM-VIS/NIR-CCD High sensitivity																									8 (λ=320 to 900 nm)	Back-thinned typ				
C10083CAH	Mini-sp TM ser	TM-VIS/NIR-CCD High resolution																									1* (λ=320 to 900 nm)	CCD image sense				
C10083MD	1	TM-VIS/NIR-MOS Wide dynamic range			32	20 t	:0 1	00	0																		8	CMOS linear image sensor				
C11697MA	1	TM-VIS/NIR-MOS-II Trigger-compatible																									8	CMOS image sense with amp array				
C9404CA		TG-UV-CCD High sensitivity	2	10 to 10	0																						3	Back-thinned typ				
C9404CAH	meter	TG-UV-CCD High resolution	200)0 to 40	U																						1	CCD image sens				
C9405CB	spectrometer sries	TG-SWNIR-CCD-II IR-enhanced				5	500	to	110	0																	5 (λ=550 to 900 nm)	IR-enhanced back-thinned type CCD image sense				
C11713CA	Mini- spec TG series	TG-RAMAN-I High resolution					50	0 t	io 60																		0.3*	Back-thinned typ				
C11714CA		TG-RAMAN-II High resolution								79	0 to	9	20														0.3*	CCD image sen				
C11482GA	ter	TG2-NIR Non-cooled type									90		io 1	700		_											7	InGaAs linear				
C9913GC	Mini-spectrometer	TG-cooled NIR-I Low noise (cooled type)																									7					
C9914GB	ni-spe serie	TG-cooled NIR-II Low noise (cooled type)											-	11	.00	to	22(00									8	image sensor				
C11118GA		TG-cooled NIR-III Low noise (cooled type)													90	0 to	o 2	55(0								20					
C11007MA	Mini- spectrometer RC series	RC-VIS-MOS Spectrometer module			340	to 🛛	780																				9	CMOS linear image sensor				
C11008MA	Mini- spe RC series	RC-SWNIR-MOS Spectrometer module					64) to	o 105	50																	8	IR-enhanced CMOS linear image sensor				
Typ.	bilo m	ooguromont ogui		.t																												
Installation into mol		_	Jinei	it.	_						Spe	ecti	ral ı	esp	oon	se	ran	ige	(n	m)							Spectral resolution max.	Imago concor				
	cter	Type RC-VIS-MOS	200		00	60		πT	0 10	000) 12	200	14	00	160	00	180	00	200	00	220	0	240	0 2	260	0	(nm)	Image sensor CMOS linear				
C11009MA	Mini- spectrometer RC series	Spectrometer head RC-SWNIR-MOS		_	340	to	780																_				9	image sensor IR-enhanced				
C11010MA	Mini- s RC ser	Spectrometer head					64) to	o 10	50																	8	CMOS linear image sensor				
Installation into mol	bile m	easurement equi	omei	nt (u	Itra-	con	npad	t)																								
Type no.		Туре	20) ∠	100	60	0	80	0 1				ral 1) 14								220	0	240	0 2	260		Spectral resolution max. (nm)	Image sensor				
C10988MA-01	Mini- spectrometer MS series	MS-VIS-MOS Spectrometer head			340	to 7	750																				14	CMOS linear				
C11708MA	Mini- spe. MS series	MS-SWNIR-MOS Spectrometer head					64) to	o 105	50																	20	image sensor				
C12666MA	Micro- spectrometer	Spectrometer head			340	to	780				Τ																15	CMOS linear image sensor				



Related information

www.hamamatsu.com/sp/ssd/doc en.html

- Precautions
 - Notice

Technical information

· Mini-spectrometer / Technical information

Information described in this material is current as of March, 2014.

Product specifications are subject to change without prior notice due to improvements or other reasons. This document has been carefully prepared and the information contained is believed to be accurate. In rare cases, however, there may be inaccuracies such as text errors. Before using these products, always contact us for the delivery specification sheet to check the latest specifications.

Type numbers of products listed in the delivery specification sheets or supplied as samples may have a suffix "(X)" which means preliminary specifications or a suffix "(Z)" which means developmental specifications.

The product warranty is valid for one year after delivery and is limited to product repair or replacement for defects discovered and reported to us within that one year period. However, even if within the warranty period we accept absolutely no liability for any loss caused by natural disasters or improper product use.

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